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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	CANbus, I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	72
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str731fv0t6

2 Overview

Table 2. Product overview

Features	STR730FZx		STR735FZx		STR731FVx			STR736FVx		
Flash memory - bytes	128K	256K	128K	256K	64K	128K	256K	64K	128K	256K
RAM - bytes	16 K				16 K					
Peripheral functions	10 TIM timers, 112 I/Os, 32 wake-up lines, 16 ADC				6 TIM timers, 72 I/Os, 18 wake-up lines, 12 ADC channels					
CAN peripherals	3		0		3			0		
Operating voltage	4.5 to 5.5 V									
Operating temperature	-40 to +85°C/-40 to +105° C									
Packages	**T**=TQFP144 20 x 20 **H**=LFBGA144 10 x10				**T**=TQFP100 14x14					

Package choice: reduced pin-count TQFP100 or feature-rich 144-pin TQFP or LFBGA

The STR73xF family is available in 3 packages. The TQFP144 and LFBGA144 versions have the full set of all features. The 100-pin version has fewer timers, I/Os and ADC channels. Refer to the Device Summary on Page 1 for a comparison of the I/Os available on each package.

The family includes versions with and without CAN.

High speed Flash memory

The Flash program memory is organized in 32-bit wide memory cells which can be used for storing both code and data constants. It is accessed by CPU with zero wait states @ 36 MHz.

The STR7 embedded Flash memory can be programmed using in-circuit programming or in-application programming.

The Flash memory endurance is 10K write/erase cycles and the data retention is 20 years @ 85° C.

IAP (in-application programming): IAP is the ability to re-program the Flash memory of a microcontroller while the user program is running.

ICP (in-circuit programming): ICP is the ability to program the Flash memory of a microcontroller using JTAG protocol while the device is mounted on the user application board.

The Flash memory can be protected against different types of unwanted access (read/write/erase). There are two types of protection:

- Sector write protection
- Flash debug protection (locks JTAG access)

Flexible power management

To minimize power consumption, you can program the STR73xF to switch to SLOW, WFI LPWFI, STOP or HALT modes depending on the current system activity in the application.

Flexible clock control

Two clock sources are used to drive the microcontroller, a main clock driven by an external crystal or ceramic resonator and an internal backup RC oscillator that operates at 2 MHz or 32 kHz. The embedded PLL can be configured to generate an internal system clock of up to 36 MHz. The PLL output frequency can be programmed using a wide selection of multipliers and dividers.

Voltage regulators

The STR73xF requires an external 4.5 to 5.5 V power supply. There are two internal Voltage Regulators for generating the 1.8 V power supply needed by the core and peripherals. The main VR is switched off and the Low Power VR switched on when the application puts the STR73xF in Low Power Wait for Interrupt (LPWFI) mode.

Low voltage detectors

The voltage regulator and Flash modules each have an embedded LVD that monitors the internal 1.8 V supply. If the voltage drops below a certain threshold, the LVD will reset the STR73xF.

Note: An external power-on reset must be provided ensure the microcontroller starts-up correctly.

2.1 On-chip peripherals

CAN interfaces

The three CAN modules are compliant with the CAN specification V2.0 part B (active). The bit rate can be programmed up to 1 MBaud. These are not available in the STR735 and STR736.

DMA

4 DMA controllers, each with 4 data streams manage memory to memory, peripheral to peripheral, peripheral to memory and memory to peripheral transfers. The DMA requests are connected to TIM timers, BSPI0, BSPI1, BSPI2 and ADC. One of the streams can be configured to be triggered by a software request, independently from any peripheral activity.

16-bit timers (TIM)

Each of the ten timers (six in 100-pin devices) have a 16-bit free-running counter with 7-bit prescaler, up to two input capture/output compare functions, a pulse counter function, and a PWM channel with selectable frequency. This provides a total of 16 independent PWMs (12 in 100-pin devices) when added with the PWM modules (see next paragraph).

PWM modules (PWM)

The six 16-bit PWM modules have independently programmable periods and duty-cycles, with 5+3 bit prescaler factor.

Timebase timers (TB)

The three 16-bit timebase timers with 8-bit prescaler for general purpose time triggering operations.

Real-time clock (RTC)

The RTC provides a set of continuously running counters driven by separate clock signal derived from the main oscillator. The RTC can be used as a general timebase or

3 Block diagram

Figure 1. STR730F/STR735F block diagram

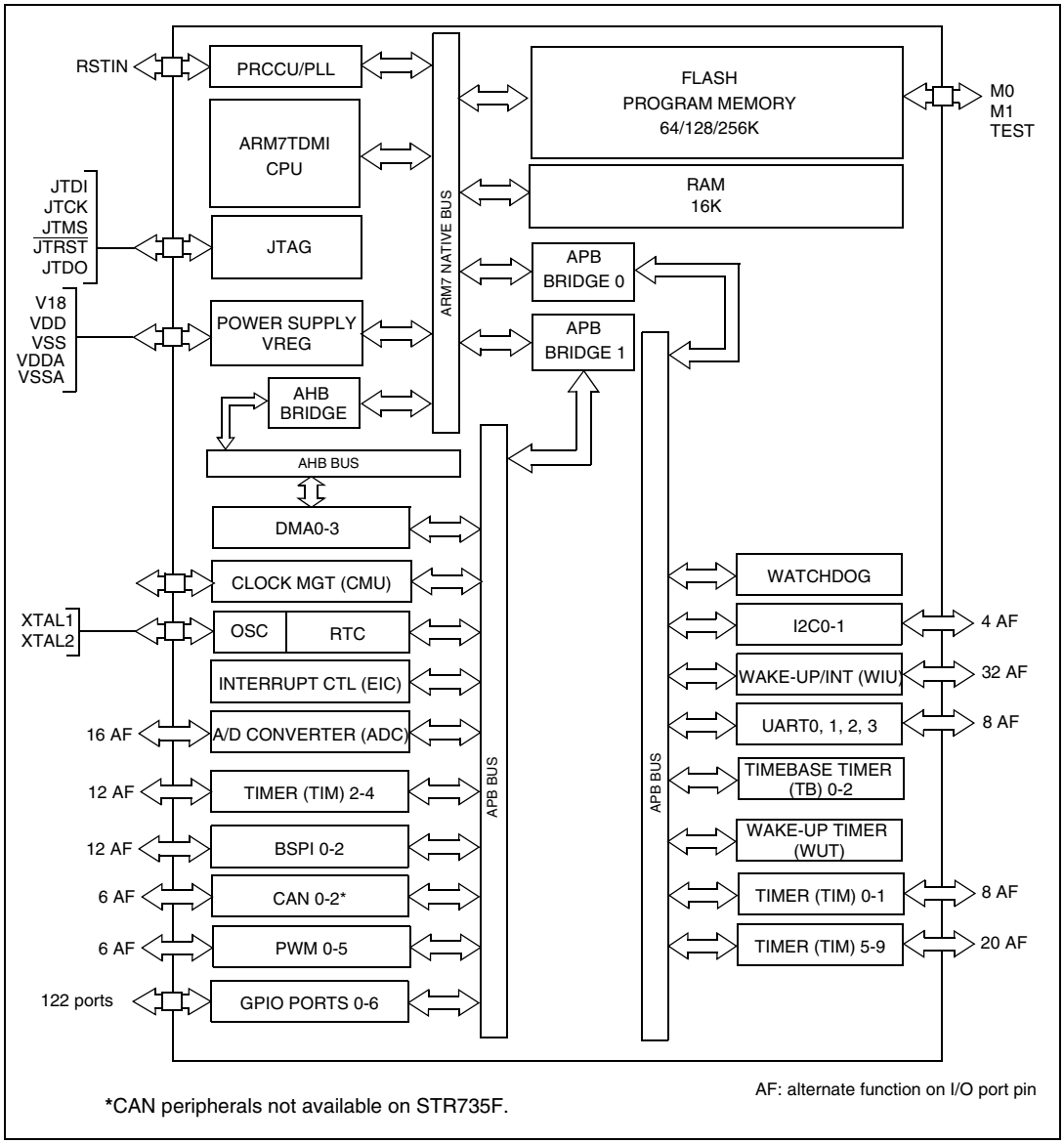
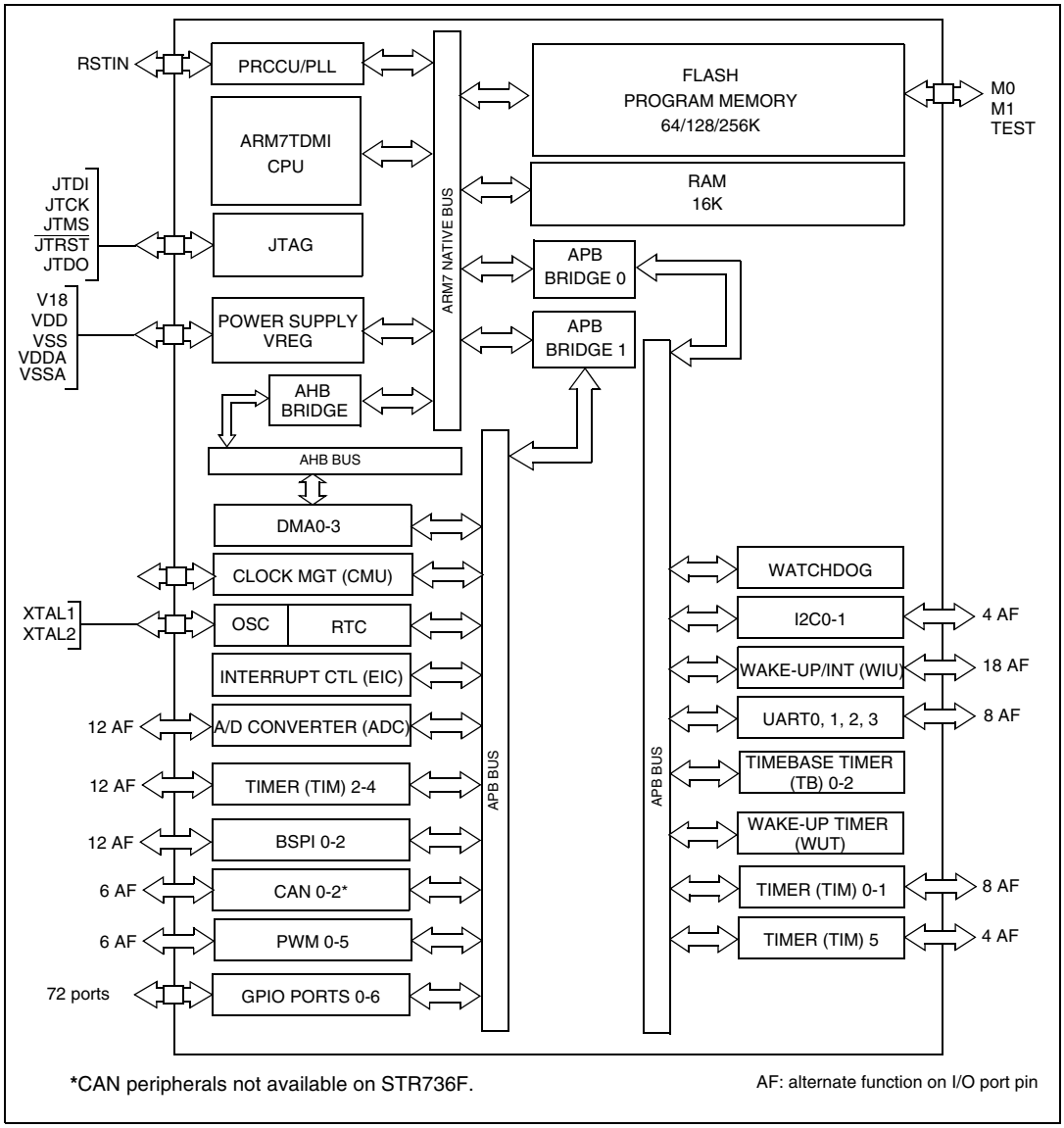


Figure 2. STR731F/STR736 block diagram



*CAN peripherals not available on STR736F.

AF: alternate function on I/O port pin

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
50	J5	36	V_{DD}	S							Supply voltage (5 V)		
51	M6	37	V_{SS}	S							Ground		
52	M7	38	XTAL1	I							Oscillator amplifier circuit input and internal clock generator input.		
53	H5	39	XTAL2	O							Oscillator amplifier circuit output.		
54	L6	40	V_{SS}	S							Ground		
55	K6	41	P2.8/TDO1/CAN2RX	I/O	T_T			2mA	X	X	Port 2.8	UART1: transmit data output	CAN2: receive data input (TQFP100 only)
56	J6	42	P2.9/RDI1/CAN2TX	I/O	T_T		WUP14	2mA	X	X	Port 2.9	UART1: receive data input	CAN2: transmit data output (TQFP100 only)
57	H6		P2.10	I/O	T_T		WUP16	2mA	X	X	Port 2.10		
58	G6		P2.11	I/O	T_T		WUP17	2mA	X	X	Port 2.11		
59	L7		P2.12	I/O	T_T		INT14	2mA	X	X	Port 2.12		
60	K7		P2.13	I/O	T_T		INT15	2mA	X	X	Port 2.13		
61	J7	43	P2.14/SCL0	I/O	T_T		WUP15	2mA	X	X	Port 2.14	I2C0: serial clock	
62	H7	44	P2.15/SDA0	I/O	T_T			2mA	X	X	Port 2.15	I2C0: serial data	
63	M8	45	Test	I		pd					Reserved pin. Must be tied to ground		
64	L8	46	V_{BIAS}	S							Internal RC oscillator bias. A 1.3 MΩ external resistor has to be connected to this pin when a 32 kHZ RC oscillator frequency is used.		
65	M10	47	V_{SS}	S							Ground		
66	M11	48	V_{DD}	S							Supply voltage (5 V)		
67	K8		P3.0/AIN0	I/O	T_T			2mA	X	X	Port 3.0	ADC: analog input 0	
68	J8		P3.1/AIN1	I/O	T_T			2mA	X	X	Port 3.1	ADC: analog input 1	
69	M9		P3.2/AIN2	I/O	T_T			2mA	X	X	Port 3.2	ADC: analog input 2	
70	L9		P3.3/AIN3	I/O	T_T			2mA	X	X	Port 3.3	ADC: analog input 3	
71	K9	49	P3.4/AIN4	I/O	T_T			2mA	X	X	Port 3.4	ADC: analog input 4 (AIN0 in TQFP100)	
72	L10	50	P3.5/AIN5	I/O	T_T			2mA	X	X	Port 3.5	ADC: Analog input 5 (AIN1 in TQFP100)	

Table 4. STR73xF pin description

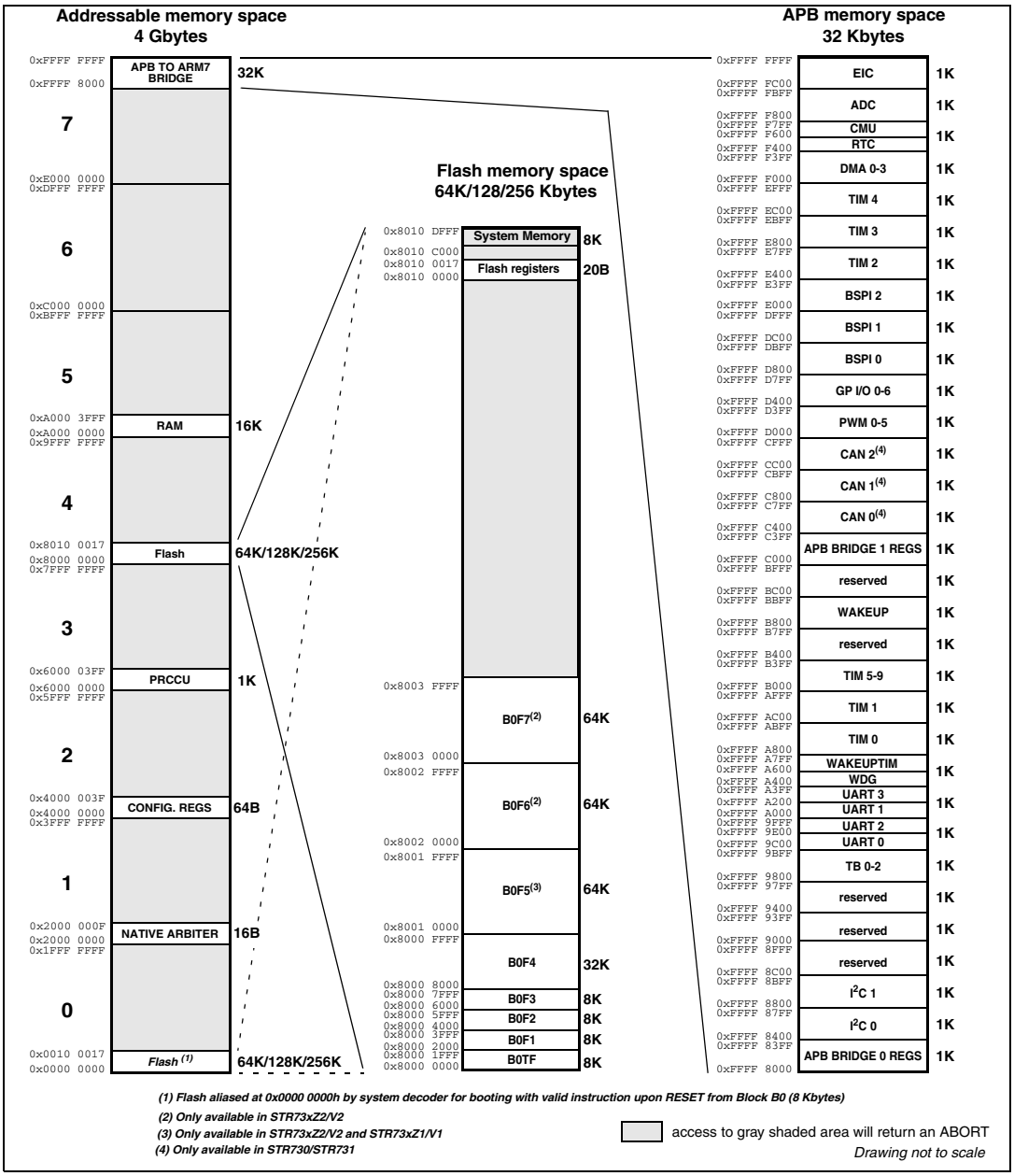
Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
97	F9		P4.3/ICAPB8	I/O	T_T		WUP27	2mA	X	X	Port 4.3	TIM8: input capture B input	
98	F8		P4.4/CAN2TX	I/O	T_T			2mA	X	X	Port 4.4	CAN2: transmit data output	
99	E12		P4.5/CAN2RX	I/O	T_T		WUP18	2mA	X	X	Port 4.5	CAN2: receive data input	
100	E11	72	P4.6/SCL1	I/O	T_T		WUP19	2mA	X	X	Port 4.6	I2C1: serial clock	
101	C12	73	P4.7/SDA1	I/O	T_T			2mA	X	X	Port 4.7	I2C1: serial data	
102	B12		P4.8/OCMPA8	I/O	T_T			2mA	X	X	Port 4.8	TIM8: output compare A output	
103	E10		P4.9/ICAPB6	I/O	T_T			2mA	X	X	Port 4.9	TIM6: input capture B input	
104	E9	74	P4.10/ICAPA6/ICAPB5	I/O	T_T		WUP20	2mA	X	X	Port 4.10	TIM6: input capture A input (144-pin pkg only)	TIM5: input capture B input (TQFP100 only)
105	D12		P4.11/OCMPB8	I/O	T_T			2mA	X	X	Port 4.11	TIM8: output compare B output	
106	D11		P4.12/ICAPA9	I/O	T_T		WUP21	2mA	X	X	Port 4.12	TIM9: input capture A input	
107	D10		P4.13/ICAPB9	I/O	T_T			2mA	X	X	Port 4.13	TIM9: input capture B input	
108	C11	75	P4.14/$\overline{SS}$1	I/O	T_T			2mA	X	X	Port 4.14	BSPI1: slave select	
109	B11	76	P4.15/SCK1	I/O	T_T		WUP22	2mA	X	X	Port 4.15	BSPI1: serial clock	
110	B10	77	P5.0/MOSI1	I/O	T_T			2mA	X	X	Port 5.0	BSPI1: master output/slave input	
111	C10	78	P5.1/MISO1	I/O	T_T			2mA	X	X	Port 5.1	BSPI1: master input/Slave output	
112	A9		P5.2/OCMPA9	I/O	T_T			2mA	X	X	Port 5.2	TIM9: output compare A output	
113	B9		P5.3/OCMPB9	I/O	T_T			2mA	X	X	Port 5.3	TIM9: output compare B output	
114	C9	79	P5.4/$\overline{SS}$2/PWM3	I/O	T_T			2mA	X	X	Port 5.4	BSPI2: slave select	PWM3: PWM output (TQFP100 only)
115	D9	80	P5.5/SCK2	I/O	T_T		WUP23	2mA	X	X	Port 5.5	BSPI2: serial clock	
116	A11	81	P5.6/MOSI2	I/O	T_T			2mA	X	X	Port 5.6	BSPI2: master output/slave input	
117	A10	82	P5.7/MISO2	I/O	T_T			2mA	X	X	Port 5.7	BSPI2: master input/slave output	
118	A8	83	P5.8/PWM4	I/O	T_T		INT6	2mA	X	X	Port 5.8	PWM4: PWM output (TQFP100 only)	

3.3 Memory mapping

Figure 5 shows the various memory configurations of the STR73xF system. The system memory map (from 0x0000_0000 to 0xFFFF_FFFF) is shown on the left part of the figure, the right part shows maps of the Flash and APB areas. For flexibility the Flash or RAM addresses can be aliased to Block 0 addresses using the remapping feature

Most reserved memory spaces (gray shaded areas in *Figure 5*) are protected from access by the user code. When an access this memory space is attempted, an ABORT signal is generated. Depending on the type of access, the ARM processor will enter “prefetch abort” state (Exception vector 0x0000_000C) or “data abort” state (Exception vector 0x0000_0010). It is up to the application software to manage these abort exceptions.

Figure 5. Memory map



4.3 Operating conditions

Subject to general operating conditions for V_{DD}, and T_A.

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	Internal CPU and system clock frequency	Accessing SRAM or Flash (zero wait state Flash access up to 36 MHz)	0	36	MHz
V_{DD}	Standard Operating Voltage		4.5	5.5	V
V_{DDA}	Operating analog reference voltage with respect to ground		4.5	V_{DD}+0.1	V
T_A	Ambient temperature range	6 partnumber suffix 7 partnumber suffix	-40 -40	85 105	°C

Table 9. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	Subject to general operating conditions for T_A.	-	20	-	ms/V

Figure 8. STOP I_{DD} vs. VDD

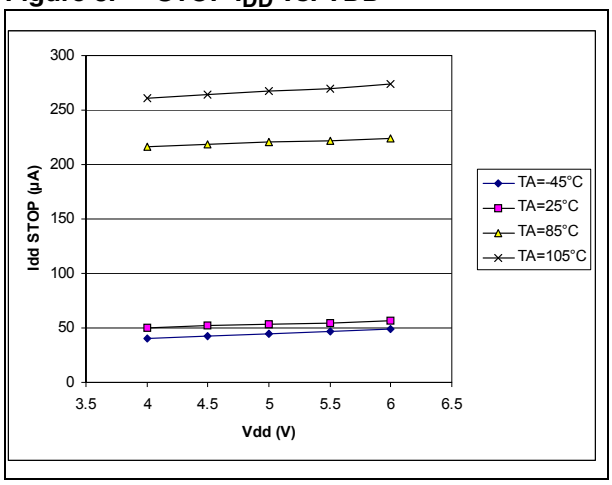


Figure 9. HALT I_{DD} vs. V_{DD}

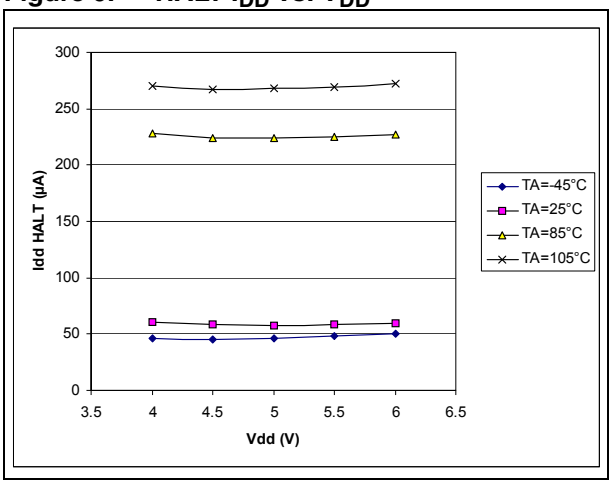


Figure 10. WFI I_{DD} vs. V_{DD}

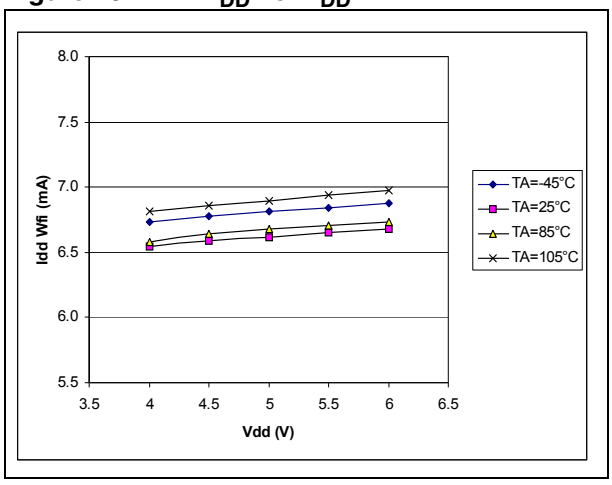
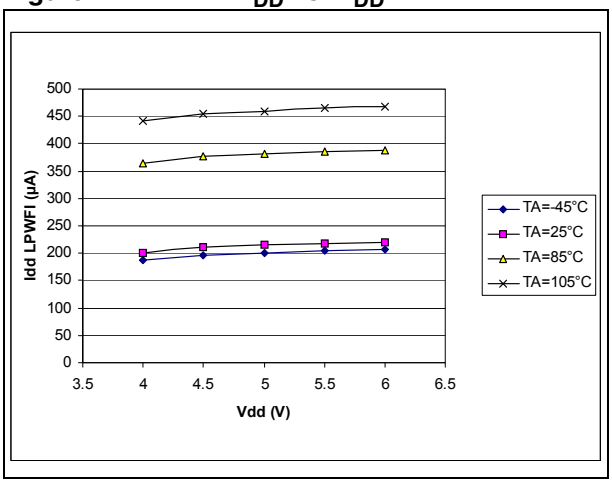


Figure 11. LPWFI I_{DD} vs. V_{DD}



Typical application current consumption

Table 11. Typical consumption in Run mode at 25°C and 85°C

Conditions		f_{MCLK} (MHz)	f_{ADC} (MHz)	Typical I_{DD} (mA)
V_{DD}= 5.5 V, RC oscillator off, PLL on, RTC enabled, 1 Timer (TIM) running, and ADC running in scan mode.	Code executing in RAM	10	10	20
		20		29
		36	9	42
	Code executing in Flash	10	10	22
		20		32
		36	9	48

Table 12. Typical consumption in Run and low power modes at 25°C

Mode	Conditions	f_{MCLK}	Typical I_{DD}
RUN	All peripherals on, RAM execution	36 MHz	76 mA
		24 MHz	56 mA
WFI	Main voltage regulator on, Flash on, EIC on, WIU on, GPIOs on.	36 MHz	33 mA
		24 MHz	31 mA
SLOW	PLL off, main voltage regulator on	4 MHz	11 mA
	CLOCK2/16, main voltage regulator on	250 kHz	8 mA
	CLOCK2/16, main voltage regulator off	250 kHz	3 mA
	RC oscillator running in low frequency, main crystal oscillator off, main voltage regulator off	29 kHz	2.5 mA
LPWFI	CLOCK2/16, main voltage regulator off, LP voltage regulator = 2 mA, Flash in power down mode.	250 kHz	528 µA
STOP	Main voltage regulator off, RTC on, RC oscillator off, LP voltage regulator = 6 mA	-	378 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 6 mA	-	83 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 4 mA	-	64 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 2 mA	-	44 µA
HALT	RTC off, LP voltage regulator = 2 mA	-	44 µA

On-chip peripherals

Table 13. Peripheral current consumption at T_A= 25°C

Symbol	Parameter	Conditions	Typ	Unit
$I_{DD(RC)}$	RC (backup oscillator) supply current	High frequency	120	µA
		Low frequency	60	µA
$I_{DD(TIM)}$	TIM timer supply current [1]	f_{MCLK}=36 MHz	350	µA
$I_{DD(BSPI)}$	BSPI supply current [1]		1.1	mA
$I_{DD(UART)}$	UART supply current [1]		850	µA
$I_{DD(I2C)}$	I2C supply current [1]		430	µA
$I_{DD(ADC)}$	ADC supply current when converting [2]		5	mA
$I_{DD(EIC)}$	EIC supply current		2.88	mA
$I_{DD(CAN)}$	CAN supply current [1]		2.95	mA
$I_{DD(GPIO)}$	GPIO supply current		150	µA
$I_{DD(TB)}$	TB supply current		250	µA
$I_{DD(PWM)}$	PWM supply current		240	µA
$I_{DD(RTC)}$	RTC supply current		370	µA
$I_{DD(DMA)}$	DMA supply current		2.5	mA
$I_{DD(ARB)}$	Native arbiter supply current		180	µA
$I_{DD(AHB)}$	AHB arbiter supply current		570	µA
$I_{DD(WUT)}$	WUT supply current		300	µA
$I_{DD(WIU)}$	WIU supply current		460	µA

1. Data based on a differential I_{DD} measurement between the on-chip peripheral when kept under reset, not clocked and the on-chip peripheral when clocked and not kept under reset. This measurement does not include the pad toggling consumption.
2. Data based on a differential I_{DD} measurement between reset configuration and continuous A/D conversions.

Table 14. Main oscillator characteristics (continued)

Symbol	Parameter	Conditions		Value			Unit
				Min	Typ	Max	
R_F [1]	Feedback resistor	f_{OSC} = 4 MHz Cp[2] = 10 pF	C_1[3] = C_2 [4]= 10 pF	150	555	-	Ω
			$C_1 = C_2$ = 20 pF	490	1035	-	
			$C_1 = C_2$ = 30 pF	490	1030	-	
			$C_1 = C_2$ = 40 pF	380	850	-	
		f_{OSC} = 5 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	470	-	
			$C_1 = C_2$ = 20 pF	415	800	-	
			$C_1 = C_2$ = 30 pF	340	735	-	
			$C_1 = C_2$ = 40 pF	260	580	-	
		f_{OSC} = 6 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	415	-	
			$C_1 = C_2$ = 20 pF	325	640	-	
			$C_1 = C_2$ = 30 pF	250	550	-	
			$C_1 = C_2$ = 40 pF	180	420	-	
		f_{OSC} = 7 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	375	-	
			$C_1 = C_2$ = 20 pF	260	525	-	
			$C_1 = C_2$ = 30 pF	185	420	-	
			$C_1 = C_2$ = 40 pF	135	315	-	
		f_{OSC} = 8 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	155	340	-	
			$C_1 = C_2$ = 20 pF	210	435	-	
			$C_1 = C_2$ = 30 pF	145	335	-	
			$C_1 = C_2$ = 40 pF	100	245	-	

1. Min and max values are guaranteed by characterization, not tested in production.
2. C_P represents the total capacitance between XTAL1 and XTAL2, including the shunt capacitance of the external quartz crystal as well as the total board parasitic cross-capacitance between XTAL1 track and XTAL2 track.
3. C_1 represents the total capacitance between XTAL1 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL1 track and ground (this includes application board track capacitance to ground and device pin capacitance).
4. C_2 represents the total capacitance between XTAL2 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL2 track and ground (this includes application board track capacitance to ground and device pin capacitance).

PLL electrical characteristics

V_{DD} = 5 V ± 10%, T_A = -40° C to T_{Amax}, unless otherwise specified

Table 16. PLL characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{PLLIN} (1)	PLL reference clock	FREF_RANGE = '0' FREF_RANGE = '1'	1.5 3.0		3.0 5.0	MHz
f_{PLLOUT}	PLL output clock	MX = "00" MX = "01" MX = "10" MX = "11"	20 x f_{PLLIN} 12 x f_{PLLIN} 28 x f_{PLLIN} 16 x f_{PLLIN}			MHz
f_{MCLK}	System clock	DX = 1..7	f_{PLLOUT}/DX		36	MHz
f_{FREE} (2)	PLL free running frequency	FREF_RANGE = '0', MX0 = '1' FREF_RANGE = '0', MX0 = '0' FREF_RANGE = '1', MX0 = '1' FREF_RANGE = '1', MX0 = '0'		120 240 240 480		kHz
t_{LOCK} (3)	PLL lock time	Stable oscillator (f_{PLLIN} = 4 MHz), stable V_{DD}		100	300	µs
Δt_{PKJIT}	PLL jitter (pk to pk)	f_{PLLIN} = 4 MHz (pulse generator)			1.5	ns

1. f_{PLLIN} is obtained from f_{OSC} directly or through an optional divider by 2.
2. Typical data are based on T_A=25°C, V_{DD}=5V
3. Max value is guaranteed by characterization, not tested in production.

Table 17. Low-power mode wake-up timing

Symbol	Parameter	Conditions	Typ	Unit
t_{WUHALT}	Wake-up from HALT mode		200	µs
t_{WUSTOP}	Wake-up from STOP mode	RC high frequency in STOP mode	180	µs
		RC low frequency in STOP mode	234	µs
$t_{WULPWFI}$ 1)	Wake-up from LPWFI mode	Main voltage regulator on RC oscillator off f_{OSC} = 4 MHz, f_{MCLK}= f_{OSC}/16 RAM or FLASH execution	27	µs
		Main voltage regulator on RC oscillator = high frequency Flash execution	46	µs
		Main voltage regulator on RC oscillator = low frequency Flash execution	3.6	ms

1. Flash memory programmed to enter Power Down mode during LPWFI.

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-4	4A

sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

- **DLU**: Electrostatic discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Table 22. Electrical sensitivities

Symbol	Parameter	Conditions	Class [1]
LU	Static latch-up class	T_A=+25°C T_A=+85°C T_A=+105°C	A A A
DLU	Dynamic latch-up class	V_{DD}= 5.5 V, f_{OSC4M} = 4 MHz, f_{MCLK} = 32 MHz, T_A = +25° C	A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

NRSTIN pin

The NRSTIN pin input driver is CMOS. A permanent pull-up is present which is the same as R_{PU} (see *: General characteristics on page 38*)

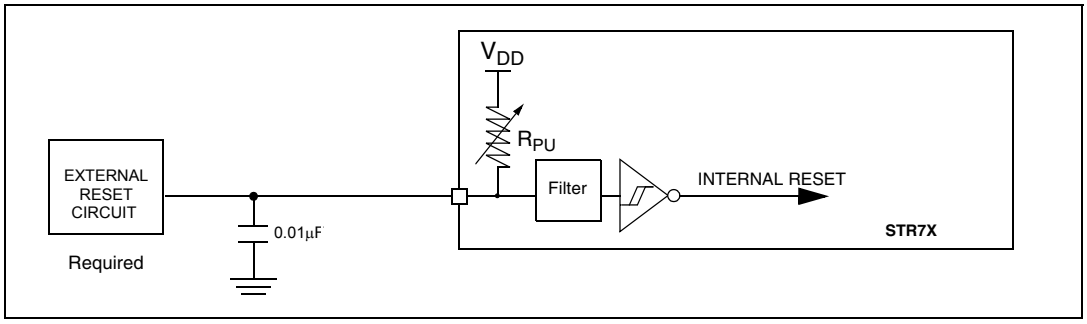
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 25. Reset pin characteristics

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$V_{IL(NRSTIN)}$	NRSTIN Input low level voltage [1]				0.3 V_{DD}	V
$V_{IH(NRSTIN)}$	NRSTIN Input high level voltage [1]		0.7 V_{DD}			
$V_{hys(NRSTIN)}$	NRSTIN Schmitt trigger voltage hysteresis [2]			800		mV
$V_{F(RSTINn)}$	NRSTIN Input filtered pulse[3]				500	ns
$V_{NF(RSTINn)}$	NRSTIN Input not filtered pulse[3]		2			µs
$V_{RP(RSTINn)}$	NRSTIN removal after Power-up[3]		100			µs

1. Data based on characterization results, not tested in production.
2. Hysteresis voltage between Schmitt trigger switching levels.
3. Data guaranteed by design, not tested in production.

Figure 19. Recommended NRSTIN pin protection[1]



1. The R_{PU} pull-up equivalent resistor is based on a resistive transistor.
2. The reset network protects the device against parasitic resets.
3. The user must ensure that the level on the NRSTIN pin can go below the $V_{IL(NRSTIN)}$ max. level specified in *Table 25*. Otherwise the reset will not be taken into account internally.

4.3.6 10-bit ADC characteristics

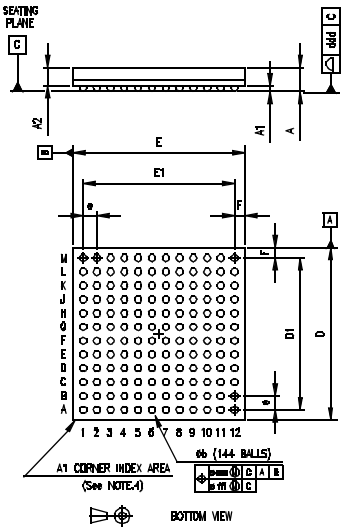
Subject to general operating conditions for V_{DDA}, f_{MCLK}, and T_A unless otherwise specified.

Table 26. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
f_{ADC}			0.4		10	MHz
V_{AIN}	Conversion voltage range [2]		V_{SSA}		V_{DDA}	V
I_{lkg}	Negative input leakage current on analog pins	$V_{IN}<V_{SS,}$ | I_{IN} |< 400 µA on adjacent analog pin		5	6	µA
C_{ADC}	Internal sample and hold capacitor				3.5	pF
t_{CAL} [2]	Calibration time	f_{ADC} = 10 MHz	580.2			µs
			5802			$1/f_{ADC}$
t_S [3]	Sampling time	f_{ADC} = 10 MHz	1		14	µs
t_{CONV}	Total conversion time (including sampling time)	f_{ADC} = 10 MHz	3			µs
			30 (10 for sampling +20 for successive approximation)			$1/f_{ADC}$
I_{ADC}	Running mode	Normal mode			5	mA
	Power-down mode				1	µA

1. Unless otherwise specified, typical data are based on T_A=25°C and V_{DDA}-V_{SS}=5.0V. They are given only as design guidelines and are not tested.
2. Calibration is recommended once after each power-up.
3. During the sample time the input capacitance C_{AIN} (6.8 max) can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sample time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

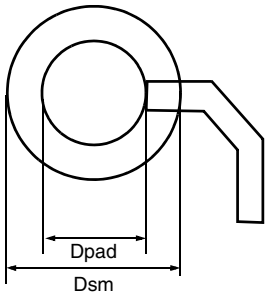
Figure 26. 144-ball low profile fine pitch ball grid array package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	1.21		1.70	0.0476		0.0669
A1	0.21			0.0083		
A2		1.085			0.0427	
b	0.35	0.40	0.45	0.0138	0.0157	0.0177
D	9.85	10.00	10.15	0.3878	0.3937	0.3996
D1		8.80			0.3465	
E	9.85	10.00	10.15	0.3878	0.3937	0.3996
E1		8.80			0.3465	
e		0.80			0.0315	
F		0.60			0.0236	
ddd			0.10			0.0039
eee			0.15			0.0059
fff			0.08			0.0031
	Number of Pins					
N	144					

[1] Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 27. Recommended PCB design rules (0.80/0.75mm pitch BGA)



Dpad	0.37 mm
Dsm	0.52 mm typ. (depends on solder mask registration tolerance
Solder paste	0.37 mm aperture diameter
– Non solder mask defined pads are recommended – 4 to 6 mils screen print	

5.2 Thermal characteristics

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \quad (1)$$

Where:

- T_A is the ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),
- P_{INT} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the chip internal power,
- $P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273°C) \quad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273°C) + \Theta_{JA} \times P_D^2 \quad (3)$$

Where:

- K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A

Table 28. Thermal characteristics

Symbol	Description	Package	Value (typical)	Unit
Θ_{JA}	Thermal resistance junction-ambient	LFBGA144	50	°C/W
		TQFP144	40	
		TQFP100	40	